# NST856BF3T5G

## **PNP General Purpose** Transistor

The NST856BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

### Features

- h<sub>FE</sub>, 220–475
- Low  $V_{CE(sat)}$ ,  $\leq -0.3 V$
- Reduces Board Space
- This is a Halide–Free Device
- This is a Pb–Free Device

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	-65	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	-100	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 1)	432	°C/W
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R <sub>ΨJL</sub> (Note 2)	143	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

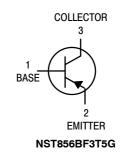
1. 100 mm<sup>2</sup> 1 oz, copper traces.

2. 500 mm<sup>2</sup> 1 oz, copper traces.



### **ON Semiconductor®**

### http://onsemi.com









M = Date Code

### **ORDERING INFORMATION**

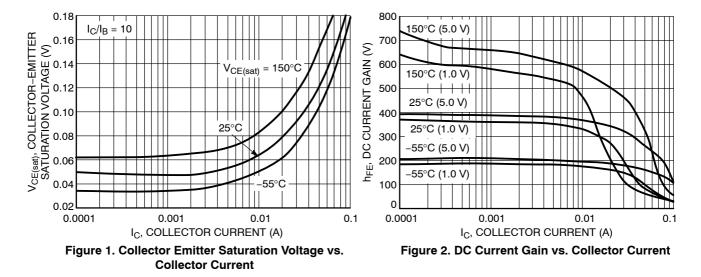
D	evice	Package	Shipping <sup>†</sup>
NST856	BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

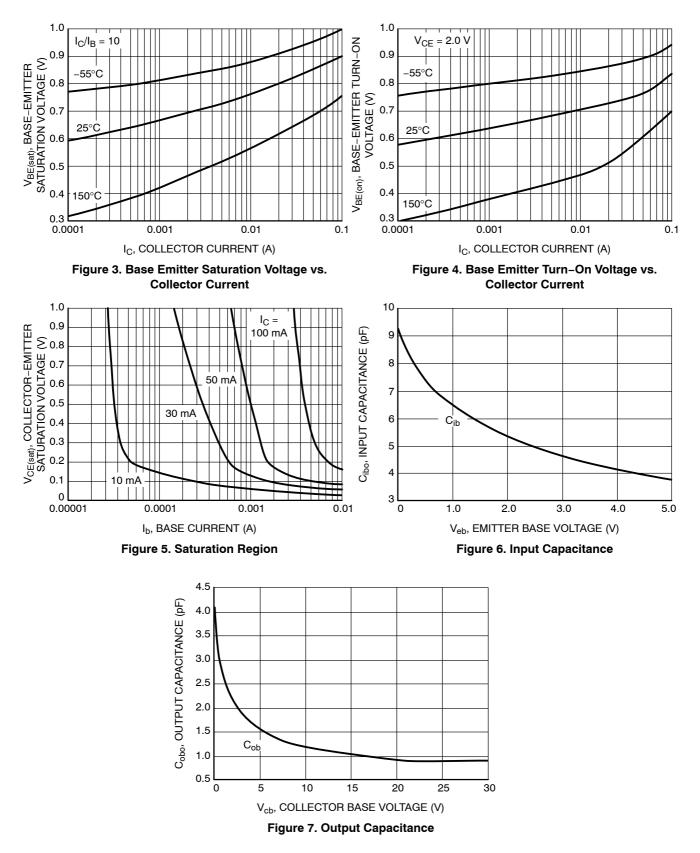
### NST856BF3T5G

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ( $I_C = -10 \text{ mA}$ )	V <sub>(BR)CEO</sub>	-65	-	-	V
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = –10 $\mu$ A, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	-80	-	-	V
Collector – Base Breakdown Voltage ( $I_C = -10 \ \mu A$ )	V <sub>(BR)CBO</sub>	-80	-	-	V
Emitter – Base Breakdown Voltage ( $I_E = -1.0 \ \mu A$ )	V <sub>(BR)EBO</sub>	-5.0	-	-	V
Collector Cutoff Current (V <sub>CB</sub> = $-30$ V) (V <sub>CB</sub> = $-30$ V, T <sub>A</sub> = $150^{\circ}$ C)	I <sub>CBO</sub>			-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = -10 $\mu$ A, V <sub>CE</sub> = -5.0 V) (I <sub>C</sub> = -2.0 mA, V <sub>CE</sub> = -5.0 V)	h <sub>FE</sub>	_ 220	150 290	_ 475	_
Collector – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>CE(sat)</sub>			-0.3 -0.8	V
Base – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>BE(sat)</sub>		-0.7 -0.9		V
Base – Emitter On Voltage $(I_{C} = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ $(I_{C} = -10 \text{ mA}, V_{CE} = -5.0 \text{ V})$	V <sub>BE(on)</sub>	-0.6		-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ( $I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz}$ )	f <sub>T</sub>	100	-	_	MHz
Output Capacitance ( $V_{CB} = -10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$ )	C <sub>obo</sub>	-	_	4.5	pF
Input Capacitance (V <sub>EB</sub> = $-0.5$ V, I <sub>C</sub> = 0 mA, f = 1.0 MHz)	C <sub>ibo</sub>	-	_	10	pF
Noise Figure (I $_C$ = –0.2 mA, V $_{CE}$ = –5.0 Vdc, R $_S$ = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB

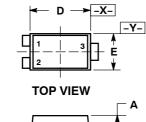


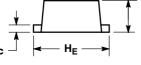
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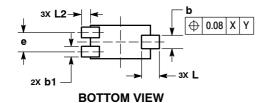
### PACKAGE DIMENSIONS

SOT-1123 CASE 524AA ISSUE C









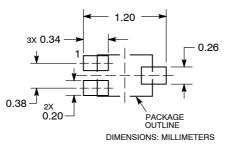
NOTES

- 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE З.
- MINIMUM THICKNESS OF BASE MATERIAL DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE 4.

MOL	D FLASI	1, PROI	ľ		
BUR	BURRS.				
	MILLIMETERS				
DIM	MIN	MAX			
Α	0.34	0.40			
b	0.15	0.28			
b1	0.10	0.20			
С	0.07	0.17			
D	0.75	0.85			
E	0.55	0.65			
е	0.35	0.40			
HE	0.95	1.05			
L	0.185 REF				
L2	0.05	0.15			

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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